

## EAST Search History

| Ref # | Hits | Search Query  | DBs                        | Default Operator | Plurals | Time Stamp       |
|-------|------|---|----------------------------|------------------|---------|------------------|
| S32 2 | 6    | S321 and ( ((different or higher or lower or greater) near3 threshold) with thickness)  | US-PGPUB; USPAT            | OR               | ON      | 2006/04/17 11:49 |
| S21 5 | 7    | S214 not S213   | US-PGPUB; USPAT            | OR               | ON      | 2006/04/17 11:49 |
| S32 5 | 8    | S324 and (@ad<"20040319" or @rlad<"20040319")   | US-PGPUB; USPAT            | OR               | ON      | 2006/04/17 11:50 |
| S32 4 | 9    | S323 not S322   | US-PGPUB; USPAT            | OR               | ON      | 2006/04/17 11:51 |
| S32 7 | 23   | S326 and (@ad<"20040319" or @rlad<"20040319")   | US-PGPUB; USPAT            | OR               | ON      | 2006/04/17 11:55 |
| S32 6 | 25   | fin\$1fet and ( (gate adj (dielectric or insulator or insulating or insulation)) with (thickness near different))                 | US-PGPUB; USPAT            | OR               | ON      | 2006/04/17 11:55 |
| S26 9 | 21   | S268 and (@ad<"20040319" or @rlad<"20040319")   | US-PGPUB; USPAT            | OR               | ON      | 2006/04/17 11:55 |
| S32 8 | 22   | S327 not S323   | US-PGPUB; USPAT            | OR               | ON      | 2006/04/17 11:56 |
| S30 9 | 0    | S308 not (S305 or S301 or S285 or S281 or S277 or S272 or S269 or S270)   | US-PGPUB; USPAT            | OR               | ON      | 2006/04/17 12:18 |
| S32 3 | 10   | S321 and ( (gate adj (dielectric or insulator or insulating or insulation)) with (thicker))                                       | US-PGPUB; USPAT            | OR               | ON      | 2006/04/25 15:56 |
| S33 1 | 0    | ( ((each or individual) adj fin) with (gate adj (dielectric or insulator or insulating or insulation or oxide)))                  | US-PGPUB; USPAT            | OR               | ON      | 2006/04/25 15:57 |
| S33 3 | 0    | ( ((each or individual) adj fin) with (gate adj (dielectric or insulator or insulating or insulation or oxide)) with (thickness)) | EPO; JPO; DERWENT; IBM_TDB | OR               | ON      | 2006/04/25 15:58 |
| S33 4 | 8    | ( (fin with (gate adj (dielectric or insulator or insulating or insulation or oxide)) with (thickness))                           | EPO; JPO; DERWENT; IBM_TDB | OR               | ON      | 2006/04/25 15:59 |
| S33 0 | 0    | ( ((each or individual) adj fin) with (gate adj (dielectric or insulator or insulating or insulation or oxide)) with (thickness)) | US-PGPUB; USPAT            | OR               | ON      | 2006/04/25 16:02 |
| S33 2 | 1    | ( (different adj fin) with (gate adj (dielectric or insulator or insulating or insulation or oxide)))                             | US-PGPUB; USPAT            | OR               | ON      | 2006/04/25 16:03 |
| S33 9 | 4    | S338 and (fin\$1fet or (fin near3 (fet or (field adj effect) or transistor or mosfet or misfet or igfet) ))                       | US-PGPUB; USPAT            | OR               | ON      | 2006/04/25 16:05 |
| S34 1 | 3    | S340 and (fin\$1fet or (fin near3 (fet or (field adj effect) or transistor or mosfet or misfet or igfet) ))                       | EPO; JPO; DERWENT; IBM_TDB | OR               | ON      | 2006/04/25 16:06 |
| S34 5 | 0    | S344 not S343   | US-PGPUB; USPAT            | OR               | ON      | 2006/04/25 16:09 |
| S34 4 | 2    | ( (thicker or thinner) with (gate adj (dielectric or insulator or insulating or insulation or oxide)) not top) and S342           | US-PGPUB; USPAT            | OR               | ON      | 2006/04/25 16:09 |
| S34 3 | 2    | ( (different adj thickness) with (gate adj (dielectric or insulator or insulating or insulation or oxide)) not top) and S342      | US-PGPUB; USPAT            | OR               | ON      | 2006/04/25 16:24 |
| S34 6 | 2    | ( (different near2 thickness) with (gate adj (dielectric or insulator or insulating or insulation or oxide)) not top) and S342    | US-PGPUB; USPAT            | OR               | ON      | 2006/04/25 16:25 |
| S35 0 | 0    | S349 not S343   | US-PGPUB; USPAT            | OR               | ON      | 2006/04/25 16:26 |
| S34 9 | 2    | ( (different near3 thickness) with (gate adj (dielectric or insulator or insulating or insulation or oxide)) not top) and S348    | US-PGPUB; USPAT            | OR               | ON      | 2006/04/25 16:26 |

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|          |    |  |                                  |    |     |                  |
|----------|----|--|----------------------------------|----|-----|------------------|
| S34<br>7 | 2  | ( (different near3 thickness) with (gate adj (dielectric or insulator or insulating or insulation or oxide)) not top) and S342                 | US-PGPUB;<br>USPAT               | OR | ON  | 2006/04/25 16:26 |
| S35<br>2 | 3  | ((thicker or thinner) with (gate adj (dielectric or insulator or insulating or insulation or oxide)) not (sidewall and top) ) and S348         | US-PGPUB;<br>USPAT               | OR | ON  | 2006/04/25 16:31 |
| S35<br>1 | 3  | ( (different near3 thickness) with (gate adj (dielectric or insulator or insulating or insulation or oxide)) not (sidewall and top) ) and S348 | US-PGPUB;<br>USPAT               | OR | ON  | 2006/04/25 16:31 |
| S35<br>8 | 0  | S357 not S352  | US-PGPUB;<br>USPAT               | OR | ON  | 2006/04/25 16:32 |
| S35<br>6 | 0  | S354 not S352  | US-PGPUB;<br>USPAT               | OR | ON  | 2006/04/25 16:32 |
| S35<br>7 | 3  | ((thicker or thinner) with (gate adj (dielectric or insulator or insulating or insulation or oxide)) not (sidewall and top) ) and S353         | US-PGPUB;<br>USPAT               | OR | ON  | 2006/04/25 17:19 |
| S36<br>1 | 0  | ( (thicker or thinner) with (gate adj (dielectric or insulator or insulating or insulation or oxide)) not top ) and S359                       | EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2006/04/25 17:21 |
| S36<br>0 | 0  | ((thicker or thinner) with (gate adj (dielectric or insulator or insulating or insulation or oxide)) not (sidewall and top) ) and S359         | EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2006/04/25 17:21 |
| S36<br>3 | 8  | ((multi or multiple) adj (channel) ) with ((fin adj fet) or fin\$1fet)   | US-PGPUB;<br>USPAT               | OR | ON  | 2006/04/25 17:27 |
| S36<br>2 | 7  | ( multi\$1finfet or ((multi or multiple) adj ((fin adj fet) or fin\$1fet) ) or multiple\$1finfet)  | US-PGPUB;<br>USPAT               | OR | ON  | 2006/04/25 17:27 |
| S36<br>6 | 0  | ( different with thickness with (gate adj (dielectric or insulator or insulating or insulation or oxide)) ) and S364                           | US-PGPUB;<br>USPAT               | OR | ON  | 2006/04/25 17:28 |
| S36<br>5 | 33 | (different with thickness with (gate adj (dielectric or insulator or insulating or insulation or oxide)) ) and S337                            | US-PGPUB;<br>USPAT               | OR | ON  | 2006/04/25 17:28 |
| S35<br>4 | 3  | ( (different near3 thickness) with (gate adj (dielectric or insulator or insulating or insulation or oxide)) not (sidewall and top) ) and S353 | US-PGPUB;<br>USPAT               | OR | ON  | 2006/04/25 17:28 |
| S36<br>7 | 1  | ((multiple\$1channel or ((several) adj (channel)) or multi\$1channel) with ((fin adj fet) or fin\$1fet) )                                      | US-PGPUB;<br>USPAT               | OR | ON  | 2006/04/25 17:29 |
| S36<br>4 | 8  | ((multiple\$1channel or ((multi or multiple) adj (channel)) or multi\$1channel) with ((fin adj fet) or fin\$1fet) )                            | US-PGPUB;<br>USPAT               | OR | ON  | 2006/04/25 17:29 |
| S33<br>7 | 33 | S336 and (fin\$1fet or (fin near3 (fet or (field adj effect) or transistor or mosfet or mstet or igfet) ) )                                    | US-PGPUB;<br>USPAT               | OR | ON  | 2006/04/26 17:43 |
| S36<br>9 | 9  | ( fins with (thicknesses or thickness) with (gate adj (dielectric or insulator or insulating or insulation or oxide)))                         | US-PGPUB;<br>USPAT               | OR | OFF | 2006/04/26 17:49 |
| S37<br>2 | 18 | S371 and (@ad<"20040319" or @rad<"20040319")   | US-PGPUB;<br>USPAT               | OR | ON  | 2006/04/26 17:50 |
| S37<br>1 | 20 | S370 not S369  | US-PGPUB;<br>USPAT               | OR | ON  | 2006/04/26 17:50 |
| S37<br>4 | 4  | S373 not S372  | US-PGPUB;<br>USPAT               | OR | ON  | 2006/04/26 17:55 |
| S37<br>3 | 4  | ( fin with (thicker or thinner) with (gate adj (dielectric or insulator or insulating or insulation or oxide)) not top)                        | US-PGPUB;<br>USPAT               | OR | ON  | 2006/04/26 17:55 |
| S37<br>6 | 2  | ( fin with ((thicknesses or thickness) near different) with (gate adj (dielectric or insulator or insulating or insulation or oxide)))         | EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2006/04/26 17:56 |

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|       |    |   |                            |    |    |                  |
|-------|----|---|----------------------------|----|----|------------------|
| S37 0 | 23 | ( fin with ((thicknesses or thickness) near different) with (gate adj (dielectric or insulator or insulating or insulation or oxide)))  | US-PGPUB; USPAT            | OR | ON | 2006/04/26 17:56 |
| S37 7 | 2  | ( (fin\$1fet or (fin near3 (fet or (field adj effect) or transistor or mosfet or misfet or igfet) ) ) with ((thicknesses or thickness) near different) with (gate adj (dielectric or insulator or insulating or insulation or oxide)))  | EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/04/26 17:57 |
| S37 8 | 4  | ( (fin\$1fet or (fin near3 (fet or (field adj effect) or transistor or mosfet or misfet or igfet) ) ) with ((thicknesses or thickness) near different) with (gate adj (dielectric or insulator or insulating or insulation or oxide)))  | US-PGPUB; USPAT            | OR | ON | 2006/04/26 17:58 |
| S38 1 | 0  | S379 and ( (thickness) with (gate adj (dielectric or insulator or insulating or insulation or oxide)) not top)  | US-PGPUB; USPAT            | OR | ON | 2006/04/26 17:59 |
| S38 0 | 0  | S379 and ( (thicker or thinner) with (gate adj (dielectric or insulator or insulating or insulation or oxide)) not top)   | US-PGPUB; USPAT            | OR | ON | 2006/04/26 17:59 |
| S37 5 | 0  | ( fin with (thicker or thinner) with (gate adj (dielectric or insulator or insulating or insulation or oxide)) not top)   | EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/04/26 17:59 |
| S37 9 | 14 | ( (fin\$1fet or (fin near3 (fet or (field adj effect) or transistor or mosfet or misfet or igfet) ) ) with (array or cell) with (periphery or peripheral))  | US-PGPUB; USPAT            | OR | ON | 2006/04/26 18:09 |
| S38 2 | 7  | ( (fin\$1fet or (fin near3 (fet or (field adj effect) or transistor or mosfet or misfet or igfet) ) ) with ((different or higher or lower) near2 threshold) )   | US-PGPUB; USPAT            | OR | ON | 2006/04/26 18:15 |
| S38 4 | 3  | ( (fin\$1fet or (fin near3 (fet or (field adj effect) or transistor or mosfet or misfet or igfet) ) ) with ((different or higher or lower) near2 (gate adj (dielectric or insulator or insulating or insulation or oxide))) )   | US-PGPUB; USPAT            | OR | ON | 2006/04/26 18:16 |
| S38 5 | 2  | ( (fin\$1fet or (fin near3 (fet or (field adj effect) or transistor or mosfet or misfet or igfet) ) ) with ((different or higher or lower) near2 (gate adj (dielectric or insulator or insulating or insulation or oxide))) )   | EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/04/26 18:19 |
| S38 8 | 1  | (fin\$1fet or (fin near3 (fet or (field adj effect) or transistor or mosfet or misfet or igfet) ) ) and ((thicker or thinner) with (gate adj (dielectric or insulator or insulating or insulation or oxide)))   | EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/04/26 18:20 |
| S38 7 | 0  | (fin\$1fet or (fin near3 (fet or (field adj effect) or transistor or mosfet or misfet or igfet) ) ) and ((thicker or thinner) near2 (gate adj (dielectric or insulator or insulating or insulation or oxide)))  | EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/04/26 18:20 |
| S38 6 | 2  | (fin\$1fet or (fin near3 (fet or (field adj effect) or transistor or mosfet or misfet or igfet) ) ) and ((different or higher or lower) near2 (gate adj (dielectric or insulator or insulating or insulation or oxide)))  | EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/04/26 18:21 |
| S38 9 | 0  | (("2nd" or second or several or many or "plurality") adj (fin\$1fet or (fin near3 (fet or (field adj effect) or transistor or mosfet or misfet or igfet) ) ) and ((different or higher or lower) near2 (gate adj (dielectric or insulator or insulating or insulation or oxide))) | EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/04/26 18:22 |
| S39 2 | 12 | (("2nd" or second or several or many or "plurality") adj (fin\$1fet or (fin near3 (fet or (field adj effect) or transistor or mosfet or misfet or igfet) ) ) and ((different or higher or lower) with (gate adj (dielectric or insulator or insulating or insulation or oxide)))  | US-PGPUB; USPAT            | OR | ON | 2006/04/26 18:23 |
| S39 1 | 0  | (("2nd" or second or several or many or "plurality") adj (fin\$1fet or (fin near3 (fet or (field adj effect) or transistor or mosfet or misfet or igfet) ) ) and ((different or higher or lower) near3 (gate adj (dielectric or insulator or insulating or insulation or oxide))) | US-PGPUB; USPAT            | OR | ON | 2006/04/26 18:23 |

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|          |    |   |                    |    |    |                  |
|----------|----|---|--------------------|----|----|------------------|
| S39<br>0 | 0  | (("2nd" or second or several or many or "plurality") adj (fin\$1fet or (fin near3 (fet or (field adj effect) or transistor or mosfet or misfet or igfet)) ) and ((different or higher or lower) near2 (gate adj (dielectric or insulator or insulating or insulation or oxide)) ) | US-PGPUB;<br>USPAT | OR | ON | 2006/04/26 18:23 |
| S39<br>6 | 4  | S395 and ((gate adj (oxide or dielectric or insulator or insulating or insulation)) with (thicker or thinner))  | US-PGPUB;<br>USPAT | OR | ON | 2006/04/30 12:44 |
| S36<br>8 | 3  | (several adj fin) and (fin\$1fet or (fin near3 (fet or (field adj effect) or transistor or mosfet or misfet or igfet)) )  | US-PGPUB;<br>USPAT | OR | ON | 2006/04/30 12:55 |
| S39<br>9 | 24 | (silicide with (capping or cap)) and (fin\$1fet or (fin near3 (fet or (field adj effect) or transistor or mosfet or misfet or igfet)) )   | US-PGPUB;<br>USPAT | OR | ON | 2006/04/30 12:56 |